High Temperature Characterization and Analysis of Silicon Carbide (SiC) Power Semiconductor Transistors

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Master of Science
In
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Hi Henry,

It was great seeing you during the CPES Conference. I hope you had a safe trip back. I found a paper that compares the performance of Cree's Gen. 1 and Gen. 2 SiC MOSFETs to 250 C (attached). At a glance, it appears that the results presented in the paper match well with mine. I hope this helps!

Also, I was wondering if I could have your permission to use some of the figures that you published in your M.S. thesis for my thesis? In particular, I was looking to use figures 2-1 (showing the curve tracer setup), and 2-8 and 2-9 (showing the turn on and turn off switching transitions). I would of course reference your thesis if you allow me to use these figures.

Best,
Christina

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Evolution of electrical performance in new generation of SiC MOSFET for high temperature applications.pdf

Zheng Chen <zchen07@vt.edu>
Thu, Apr 17, 2014 at 11:12 AM
To: Christina DiMarino <dimaricm@vt.edu>

Hi Christina,

Thanks a lot for this paper. This info is definitely what we are interested in right now and is very helpful to us.

Regarding the thesis, yes you have my permission to use these mentioned figures. Good luck with your defense by the way!

Best,
Henry